2N1671 – 2N1671A – 2N1671B

PN BAR-TYPE SILICON UNIJUNCTION TRANSISTORS

They are designed for medium-power switching, oscillator and pulse timing circuits.
Package outline is similar to TO-5 except

- Highly Stable Negative Resistance and Firing Voltage
- Low Firing Current
- High Pulse Curent Capabilities
- Simplified Circuit Design

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{B1E}	Base 1 – Emitter Reverse Voltage	2N1671 2N1671A 2N1671B	30	V
V_{B2E}	Base 2 – Emitter Reverse Voltage	2N1671 2N1671A 2N1671B	30	V
V_{B1B2}	Interbase Voltage	2N1671 2N1671A 2N1671B	35	V
I_{FRMS}	RMS Emitter Current	2N1671 2N1671A 2N1671B	50	mA
I_{EM}	Emitter Peak Current	2N1671 2N1671A 2N1671B	2	A
P_{TOT}	Total Power Dissipation	2N1671 2N1671A 2N1671B	450	mW
T_J	Maximum Junction	2N1671 2N1671A 2N1671B	150	°C
T_{STG}	Storage Temperature Range	2N1671 2N1671A 2N1671B	-55 to +150	

This data guaranteed in addition to JEDEC registered data

2N1671 – 2N1671A – 2N1671B

ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Mx	Unit
I_{EB2O}	Emitter Reverse Current	V_{B2E}=30 V, I_{B1}= 0	2N1671	-	-	-12	μA
			2N1671A	-	-	-12	
			2N1671B	-	-	-0.2	
$V_{EB1(sat)}$	Emitter saturation Voltage	V_{B2B1} = 10 V, I_E= 50 mA	2N1671	-	-	5	V
			2N1671A	-	-	5	
			2N1671B	-	-	5	
R_{BBO}	Interbase Resistance	V_{B2B1} = 3 V, , I_E= 0	2N1671	4.7	-	9.1	K□
			2N1671A	4.7	-	9.1	
			2N1671B	4.7	-	9.1	
η	Intrinsic stand-off ratio	V_{B2B1}= 10 V	2N1671	0.47	-	0.62	-
			2N1671A	0.47	-	0.62	
			2N1671B	0.47	-	0.62	
I_V	Valley Current	V_{B2B1}= 10 V, R_{B2}= 100 □	2N1671	-	-	8	mA
			2N1671A	-	-	8	
			2N1671B	-	-	8	
I_P	Peak Current	V_{B2B1}= 25 V	2N1671	-	-	25	μA
			2N1671A	-	-	25	
			2N1671B	-	-	6	

MECHANICAL DATA CASE TO-5